



# Bipolar PNP Bare Die – BTP116

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## Part Description

The BTP116 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN116

## Key Parameters:

- VCBO = -80V
- VCEO = -80V
- VEBO = -4V
- hFE = 100- @ VCE = -1V, IC = -0.1A
- VCE(Sat) = -0.25V @ IC = -0.1A, IB = -10mA
- fT = 50 MHz @ VCE = -1V, IE = 0A
- COBO = - pF @ VCB = - V

## Features

Low VCE(sat). Designed to provide performance equivalent to MPSA56 or ROHM 2SB1198K

## Die Size (Unawn)

560µm X 560µm, 22 Mils X 22 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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